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Examiner: TBA
Atty Dkt No: 00 P 9031 US
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Applicant: Tews et al.

Serial No.: 09/714,356

Filed: November 16, 2000

For: NITROGEN IMPLANTATION USING A SHADOW
EFFECT TO CONTROL GATE OXIDE THICKNESS
IN DRAM SEMICONDUCTOR

LETTER TO OFFICIAL DRAFTSMAN

Attention: Drawing Processing Branch
Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Pursuant to M.P.E.P. Section 608.02, enclosed please find two (2) sheets of formal drawings in the referenced case. These are formal versions of the informal drawings filed with the application.

If there are any informalities with these drawings, Applicant requests issuance of a Form PTO-948 identifying the informalities noted by the Official Draftsman.

Respectfully submitted,

Stanton C. Braden
Reg. No. 32,556

Date July 30, 2001

Infineon Technologies North America Corp.
c/o Siemens Corporation
Intellectual Property Department
186 Wood Avenue South
Iselin, NJ 08830
(732) 321-3015
SCB/am

CERTIFICATE OF MAILING PURSUANT TO 37 CFR § 1.8

I hereby certify that this correspondence is being deposited on July 30, 2001 with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231 on or before the date below

Date of
Signature July 30, 2001

Pamela Gewirtz

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